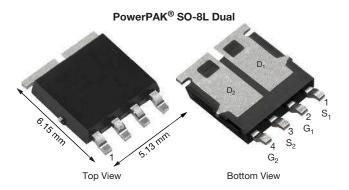
SQJ946EP



Vishay Siliconix

Automotive Dual N-Channel 40 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY	
V _{DS} (V)	40
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.033
$R_{DS(on)}$ (Ω) at V_{GS} = 4.5 V	0.039
I _D (A) per leg	15
Configuration	Dual
Package	PowerPAK SO-8L



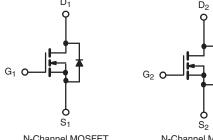
FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

D-



COMPLIANT HALOGEN FREE



N-Channel MOSFET

N-Channel MOSFET

ABSOLUTE MAXIMUM RATING	iS (T _C = 25 °C, unless	otherwise noted)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	40	V	
Gate-Source Voltage		V _{GS}	± 20	v	
Continuous Drain Current	T _C = 25 °C ª		15		
Continuous Drain Current	T _C = 125 °C	ID	11		
Continuous Source Current (Diode conduction) ^a		I _S	15	А	
Pulsed Drain Current ^b		I _{DM}	40		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	11		
Single Pulse Avalanche Energy	L = 0.1 mm	E _{AS}	6	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C	Pn	27	W	
	T _C = 125 °C	гD	9	vv	
Operating Junction and Storage Temperatu	erating Junction and Storage Temperature Range		-55 to +175	°C	
Soldering Recommendations (Peak tempera	ature) ^{d, e}		260	C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB mount ^c	R _{thJA}	85	°C/W
Junction-to-Case (Drain)		R _{thJC}	5.5	C/W

Notes

- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR4 material).
- d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

1

a. Package limited.

www.vishay.com

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StaticDrain-Source Breakdown Voltage V_{DS} $V_{GS} = 0 V$, $I_D = 250 \mu A$ Gate-Source Threshold Voltage $V_{GS}(th)$ $V_{DS} = V_{GS}$, $I_D = 250 \mu A$ Gate-Source Leakage I_{GSS} $V_{DS} = 0 V$, $V_{GS} = \pm 20 V$ Zero Gate Voltage Drain Current I_{DSS} $V_{GS} = 0 V$ $V_{DS} = 40 V$ Zero Gate Voltage Drain Current ^a $I_{D(on)}$ $V_{GS} = 0 V$ $V_{DS} = 40 V$, $T_J = 125 °C$ On-State Drain Current ^a $I_{D(on)}$ $V_{GS} = 10 V$ $V_{DS} = 40 V$, $T_J = 175 °C$ On-State Drain Current ^a $I_{D(on)}$ $V_{GS} = 10 V$ $I_D = 7 A$ Drain-Source On-State Resistance ^a $R_{DS(on)$ $V_{GS} = 10 V$ $I_D = 7 A$, $T_J = 125 °C$ VGS = 10 V $I_D = 7 A$ $V_{GS} = 10 V$ $I_D = 7 A$ Drain-Source On-State Resistance ^b g_{fs} $V_{DS} = 10 V$ $I_D = 7 A$, $T_J = 125 °C$ VGS = 10 V $I_D = 7 A$ $I_D = 7 A$ $V_{GS} = 10 V$ $I_D = 7 A$, $T_J = 125 °C$ VGS = 10 V $I_D = 7 A$ $I_D = 7 A$ $V_{GS} = 10 V$ $I_D = 7 A$ Drain-Source On-State Resistance ^b g_{fs} $V_{DS} = 15 V$, $I_D = 5 A$ Dynamic ^b $I_D = 7 A$ $V_{GS} = 0 V$ $V_{DS} = 25 V$, $f = 1 MHz$ Reverse Transfer Capacitance C_{rss} C_{rss} $V_{DS} = 20 V$, $I_D = 4 A$ Gate-Drain Charge ^c Q_{gd} Q_{gd} $V_{DS} = 20 V$, $I_D = 4 A$	40 1.5 - - - -	- 2.0 -	- 2.5		
$ \begin{array}{c c c c c c c } \hline Gate-Source Threshold Voltage & V_{GS(th)} & V_{DS} = V_{GS}, I_D = 250 \ \mu A \\ \hline Gate-Source Leakage & I_{GSS} & V_{DS} = 0 \ V, V_{GS} = \pm 20 \ V \\ \hline V_{GS} = 0 \ V & V_{DS} = 40 \ V \\ \hline V_{GS} = 0 \ V & V_{DS} = 40 \ V \\ \hline V_{GS} = 0 \ V & V_{DS} = 40 \ V, T_J = 125 \ ^{\circ}C \\ \hline V_{GS} = 0 \ V & V_{DS} = 40 \ V, T_J = 125 \ ^{\circ}C \\ \hline V_{GS} = 0 \ V & V_{DS} = 40 \ V, T_J = 175 \ ^{\circ}C \\ \hline V_{GS} = 0 \ V & V_{DS} = 40 \ V, T_J = 175 \ ^{\circ}C \\ \hline V_{GS} = 10 \ V & V_{DS} \geq 5 \ V \\ \hline V_{GS} = 10 \ V & I_D = 7 \ A \\ \hline V_{GS} = 10 \ V & I_D = 7 \ A \\ \hline V_{GS} = 10 \ V & I_D = 7 \ A \\ \hline Total Gate Charge \ ^{\circ} & Q_g \\ \hline Total Gate Charge \ ^{\circ} & Q_{gs} \\ \hline Gate Resistance \ ^{\circ} & Q_{gs} \\ \hline Gate Resistance \ ^{\circ} & Q_{gd} \\ \hline Gate Resistance \ ^{\circ} & R_g \\ \hline \end{array}$	1.5 - -	-	- 2.5		
$ \begin{array}{c c c c c c } \hline Gate-Source Leakage & I_{GSS} & V_{DS} = 0 \ V, \ V_{GS} = \pm 20 \ V \\ \hline V_{GS} = 0 \ V & V_{DS} = 40 \ V \\ \hline V_{GS} = 0 \ V & V_{DS} = 40 \ V, \ T_{J} = 125 \ ^{\circ}C \\ \hline V_{GS} = 0 \ V & V_{DS} = 40 \ V, \ T_{J} = 125 \ ^{\circ}C \\ \hline V_{GS} = 0 \ V & V_{DS} = 40 \ V, \ T_{J} = 125 \ ^{\circ}C \\ \hline V_{GS} = 0 \ V & V_{DS} = 40 \ V, \ T_{J} = 175 \ ^{\circ}C \\ \hline V_{GS} = 0 \ V & V_{DS} = 40 \ V, \ T_{J} = 175 \ ^{\circ}C \\ \hline V_{GS} = 0 \ V & V_{DS} = 5 \ V \\ \hline V_{DS} = 40 \ V, \ T_{J} = 175 \ ^{\circ}C \\ \hline V_{GS} = 10 \ V & V_{DS} \ge 5 \ V \\ \hline V_{DS} \ge 5 \ V & V_{DS} \ge 5 \ V \\ \hline V_{GS} = 10 \ V & I_{D} = 7 \ A, \ T_{J} = 125 \ ^{\circ}C \\ \hline V_{GS} = 10 \ V & I_{D} = 7 \ A, \ T_{J} = 125 \ ^{\circ}C \\ \hline V_{GS} = 10 \ V & I_{D} = 7 \ A, \ T_{J} = 125 \ ^{\circ}C \\ \hline V_{GS} = 10 \ V & I_{D} = 7 \ A, \ T_{J} = 125 \ ^{\circ}C \\ \hline V_{GS} = 10 \ V & I_{D} = 7 \ A, \ T_{J} = 125 \ ^{\circ}C \\ \hline V_{GS} = 10 \ V & I_{D} = 7 \ A, \ T_{J} = 125 \ ^{\circ}C \\ \hline V_{GS} = 10 \ V & I_{D} = 7 \ A, \ T_{J} = 125 \ ^{\circ}C \\ \hline V_{GS} = 10 \ V & I_{D} = 7 \ A, \ T_{J} = 125 \ ^{\circ}C \\ \hline V_{GS} = 10 \ V & I_{D} = 7 \ A, \ T_{J} = 175 \ ^{\circ}C \\ \hline V_{GS} = 4.5 \ V & I_{D} = 4 \ A \\ \hline Dynamic \ b & V_{DS} = 15 \ V, \ I_{D} = 5 \ A \\ \hline Dynamic \ b & V_{DS} = 25 \ V, \ f = 1 \ MHz \\ \hline Reverse \ Transfer \ Capacitance \ C_{rss} & V_{GS} = 0 \ V \\ \hline V_{DS} = 20 \ V, \ I_{D} = 4 \ A \\ \hline C_{10} \ C_$	-	-	2.5	V	
$ \begin{array}{c c c c c c } \hline Gate-Source Leakage & I_{GSS} & V_{DS} = 0 \ V, \ V_{GS} = \pm 20 \ V \\ \hline V_{GS} = 0 \ V & V_{DS} = 40 \ V \\ \hline V_{GS} = 0 \ V & V_{DS} = 40 \ V, \ T_J = 125 \ ^{\circ}C \\ \hline V_{GS} = 0 \ V & V_{DS} = 40 \ V, \ T_J = 125 \ ^{\circ}C \\ \hline V_{GS} = 0 \ V & V_{DS} = 40 \ V, \ T_J = 125 \ ^{\circ}C \\ \hline V_{GS} = 0 \ V & V_{DS} = 40 \ V, \ T_J = 175 \ ^{\circ}C \\ \hline V_{GS} = 0 \ V & V_{DS} \geq 5 \ V \\ \hline V_{DS} \geq 5 \ V & V_{DS} \geq 5 \ V \\ \hline V_{DS} \geq 5 \ V & V_{DS} \geq 5 \ V \\ \hline V_{DS} \geq 10 \ V & I_D = 7 \ A \\ \hline V_{GS} = 10 \ V & I_D = 7 \ A, \ T_J = 125 \ ^{\circ}C \\ \hline V_{GS} = 10 \ V & I_D = 7 \ A, \ T_J = 125 \ ^{\circ}C \\ \hline V_{GS} = 10 \ V & I_D = 7 \ A, \ T_J = 125 \ ^{\circ}C \\ \hline V_{GS} = 10 \ V & I_D = 7 \ A, \ T_J = 125 \ ^{\circ}C \\ \hline V_{GS} = 10 \ V & I_D = 7 \ A, \ T_J = 125 \ ^{\circ}C \\ \hline V_{GS} = 10 \ V & I_D = 7 \ A, \ T_J = 125 \ ^{\circ}C \\ \hline V_{GS} = 10 \ V & I_D = 7 \ A, \ T_J = 125 \ ^{\circ}C \\ \hline V_{GS} = 10 \ V & I_D = 7 \ A, \ T_J = 125 \ ^{\circ}C \\ \hline V_{GS} = 10 \ V & I_D = 7 \ A, \ T_J = 125 \ ^{\circ}C \\ \hline V_{GS} = 10 \ V & I_D = 7 \ A, \ T_J = 125 \ ^{\circ}C \\ \hline V_{GS} = 10 \ V & I_D = 7 \ A, \ T_J = 175 \ ^{\circ}C \\ \hline V_{GS} = 4.5 \ V \ I_D = 4 \ A \\ \hline Dupund \ Capacitance & C_{ISS} \\ \hline Dutput \ Capacitance & C_{ISS} \\ \hline Dutput \ Capacitance & C_{C_{ISS}} \\ \hline Total \ Gate \ Charge \ ^{\circ} & Q_{g} \\ \hline Gate \ Charge \ ^{\circ} & Q_{g} \\ \hline Gate \ Charge \ ^{\circ} & Q_{g} \\ \hline Gate \ Charge \ ^{\circ} & Q_{g} \\ \hline Gate \ Charge \ ^{\circ} & Q_{g} \\ \hline Gate \ Resistance & R_g \\ \hline \end{array}$		-	2.0	v	
$ \begin{array}{c c} \mbox{Zero Gate Voltage Drain Current} & I_{DSS} & \hline V_{GS} = 0 \ V & V_{DS} = 40 \ V, \ T_J = 125 \ ^{\circ}C \\ \hline V_{GS} = 0 \ V & V_{DS} = 40 \ V, \ T_J = 175 \ ^{\circ}C \\ \hline V_{GS} = 0 \ V & V_{DS} = 40 \ V, \ T_J = 175 \ ^{\circ}C \\ \hline V_{GS} = 0 \ V & V_{DS} \ge 5 \ V \\ \hline V_{DS} \ge 10 \ V & V_{DS} \ge 5 \ V \\ \hline V_{DS} \ge 10 \ V & I_D = 7 \ A \\ \hline V_{GS} = 10 \ V & I_D = 7 \ A, \ T_J = 125 \ ^{\circ}C \\ \hline V_{GS} = 10 \ V & I_D = 7 \ A, \ T_J = 125 \ ^{\circ}C \\ \hline V_{GS} = 10 \ V & I_D = 7 \ A, \ T_J = 125 \ ^{\circ}C \\ \hline V_{GS} = 10 \ V & I_D = 7 \ A, \ T_J = 125 \ ^{\circ}C \\ \hline V_{GS} = 10 \ V & I_D = 7 \ A, \ T_J = 125 \ ^{\circ}C \\ \hline V_{GS} = 10 \ V & I_D = 7 \ A, \ T_J = 125 \ ^{\circ}C \\ \hline V_{GS} = 10 \ V & I_D = 7 \ A, \ T_J = 175 \ ^{\circ}C \\ \hline V_{GS} = 4.5 \ V & I_D = 4 \ A \\ \hline \hline Dynamic \ ^{b} \\ \hline Portan \ Capacitance \ C_{iss} \\ \hline Output \ Capacitance \ C_{iss} \\ \hline Output \ Capacitance \ C_{coss} \\ \hline Total \ Gate \ Charge \ ^{\circ} \ Q_{g} \\ \hline Gate \ Charge \ ^{\circ} \ Q_{g} \\ \hline Gate \ Charge \ ^{\circ} \ Q_{g} \\ \hline Gate \ Charge \ ^{\circ} \ Q_{gg} \\ \hline Gate \ Charge \ ^{\circ} \ Q_{gg} \\ \hline Gate \ Resistance \ R_{g} \ f = 1 \ MHz \\ \hline \end{array}$			± 100	nA	
$\begin{tabular}{ c c c c } \hline V_{GS} = 0 & V & V_{DS} = 40 & V, & T_J = 175 & ^{\circ}C \\ \hline V_{GS} = 10 & V & V_{DS} \geq 5 & V \\ \hline V_{GS} = 10 & V & V_{DS} \geq 5 & V \\ \hline V_{GS} = 10 & V & I_D = 7 & A \\ \hline V_{GS} = 10 & V & I_D = 7 & A, & T_J = 125 & ^{\circ}C \\ \hline V_{GS} = 10 & V & I_D = 7 & A, & T_J = 125 & ^{\circ}C \\ \hline V_{GS} = 10 & V & I_D = 7 & A, & T_J = 175 & ^{\circ}C \\ \hline V_{GS} = 4.5 & V & I_D = 4 & A \\ \hline \end{tabular}$		-	1		
$ \begin{array}{c c c c c c c } On-State Drain Current a & I_{D(on)} & V_{GS} = 10 \ V & V_{DS} \ge 5 \ V \\ \hline V_{GS} = 10 \ V & I_D = 7 \ A \\ \hline V_{GS} = 10 \ V & I_D = 7 \ A, \ T_J = 125 \ ^{\circ}C \\ \hline V_{GS} = 10 \ V & I_D = 7 \ A, \ T_J = 125 \ ^{\circ}C \\ \hline V_{GS} = 10 \ V & I_D = 7 \ A, \ T_J = 175 \ ^{\circ}C \\ \hline V_{GS} = 4.5 \ V & I_D = 4 \ A \\ \hline \end{array} $	-	-	50	μA	
$\begin{array}{c c} P_{\rm rescaled} & P_{\rm rescaled}$		-	150		
$\begin{array}{c c} \mbox{Drain-Source On-State Resistance a} \\ \mbox{Drain-Source On-State Resistance a} \\ Rescaled of the series of$	10	-	-	Α	
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	-	0.027	0.033		
$\begin{array}{ c c c c } \hline & V_{GS} = 10 \ V & I_D = 7 \ A, \ T_J = 175 \ ^{\circ}C \\ \hline & V_{GS} = 4.5 \ V & I_D = 4 \ A \\ \hline & V_{DS} = 15 \ V, \ I_D = 4 \ A \\ \hline & Dynamic \ ^{b} \\ \hline & Dynamic \ ^{b} \\ \hline & Duput \ Capacitance & C_{iss} \\ \hline & Output \ Capacitance & C_{oss} \\ \hline & Output \ Capacitance & C_{oss} \\ \hline & Output \ Capacitance & C_{rss} \\ \hline & Output \ Capacitance & C_{rss} \\ \hline & Total \ Gate \ Charge \ ^{\circ} & Q_{g} \\ \hline & Gate \ Charge \ ^{\circ} & Q_{gd} \\ \hline & Gate \ Prain \ Charge \ ^{\circ} & Q_{gd} \\ \hline & Gate \ Resistance & R_{g} & f = 1 \ MHz \\ \hline \end{array}$	-	-	0.056		
Forward Transconductance b g_{fs} $V_{DS} = 15 \text{ V}, I_D = 5 \text{ A}$ Dynamic bInput Capacitance C_{iss} Output Capacitance C_{oss} Reverse Transfer Capacitance C_{rss} Total Gate Charge ° Q_g Gate-Source Charge ° Q_{gs} Gate-Drain Charge ° Q_{gd} Gate Resistance R_g f = 1 MHz	-	-	0.070	Ω	
Dynamic bInput Capacitance C_{iss} Output Capacitance C_{oss} Output Capacitance C_{oss} Total Gate Charge ° Q_g Gate-Source Charge ° Q_{gs} Gate-Drain Charge ° Q_{gd} Gate Resistance R_g f = 1 MHz	-	0.032	0.039	1	
$\begin{tabular}{ c c c c c } \hline Input Capacitance & C_{iss} \\ \hline Output Capacitance & C_{oss} \\ \hline Output Capacitance & C_{oss} \\ \hline Reverse Transfer Capacitance & C_{rss} \\ \hline Total Gate Charge ^{\circ} & Q_g \\ \hline Gate-Source Charge ^{\circ} & Q_{gs} \\ \hline Gate-Drain Charge ^{\circ} & Q_{gd} \\ \hline Gate Resistance & R_g \\ \hline \end{tabular} \e$	-	29	-	S	
$\begin{tabular}{ c c c c } \hline Output Capacitance & C_{oss} & $V_{GS} = 0 V & $V_{DS} = 25 V, $f = 1 MHz \\ \hline Reverse Transfer Capacitance & C_{rss} & $V_{GS} = 0 V & $V_{DS} = 25 V, $f = 1 MHz \\ \hline Total Gate Charge $^{\circ}$ & Q_g & $V_{GS} = 10 V & $V_{DS} = 20 V, $I_D = 4 A & $Gate-Drain Charge $^{\circ}$ & Q_{gd} & $V_{GS} = 10 V & $V_{DS} = 20 V, $I_D = 4 A & $Gate Resistance$ & R_g & $f = 1 MHz & $f = 1 MHz & $f = 1 MHz & MHz & $f = 1 MHz & MHz & $f = 1 MHz & $					
$\begin{tabular}{ c c c c c } \hline Reverse Transfer Capacitance & C_{rss} & $$ $$ $$ $$ $$ $$ $$ $$ $$ $$ $$ $$ $	-	395	600		
$\begin{tabular}{ c c c c } \hline Total Gate Charge `` $$Q_g$ \\ \hline Gate-Source Charge `` $$Q_{gs}$ \\ \hline $V_{GS} = 10 $$V$ $$V_{DS} = 20 $$V$, $I_D = 4 $$A$ \\ \hline $Gate-Drain Charge `` $$Q_{gd}$ \\ \hline $Gate Resistance$ $$R_g$ $$f = 1 $$MHz$ \\ \hline \end{tabular}$	-	60	85	pF	
$\begin{tabular}{ c c c c } \hline Total Gate Charge `` $$Q_g$ \\ \hline Gate-Source Charge `` $$Q_{gs}$ \\ \hline $V_{GS} = 10 $$V$ $$V_{DS} = 20 $$V$, $I_D = 4 $$A$ \\ \hline $Gate-Drain Charge `` $$Q_{gd}$ \\ \hline $Gate Resistance$ $$R_g$ $$f = 1 $$MHz$ \\ \hline \end{tabular}$	-	25	40		
Gate-Drain Charge ° Q_{gd} Gate Resistance R_g f = 1 MHz	-	10	20		
Gate Resistance R _g f = 1 MHz	-	1.4	-	nC	
	-	2.2	-		
	2	4.2	6.5	Ω	
Turn-On Delay Time ^c t _{d(on)}	-	7	15		
Rise Time ^c t_r $V_{DD} = 20 \text{ V}$, $R_l = 5 \Omega$	-	3	10		
Turn-Off Delay Time c $t_{d(off)}$ $I_D \cong 4$ Å, $V_{GEN} = 10$ V, $R_g = 1$ Ω	-	14	30	ns	
Fall Time ^c t _f	-	2	5	1	
Source-Drain Diode Ratings and Characteristics ^b		•			
Pulsed Current ^a I _{SM}	-	-	40	Α	
Forward Voltage V_{SD} $I_F = 7 \text{ A}, V_{GS} = 0 \text{ V}$		0.88	1.2	V	

Notes

a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$

b. Guaranteed by design, not subject to production testing.

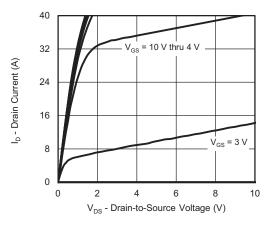
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

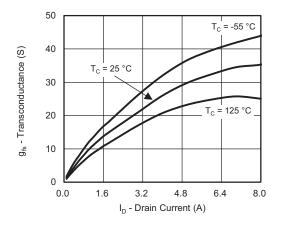
2



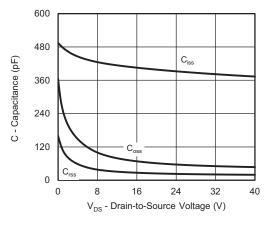
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



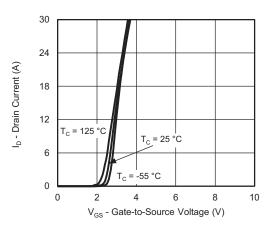
Output Characteristics



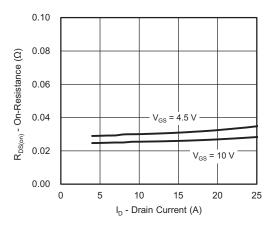
Transconductance



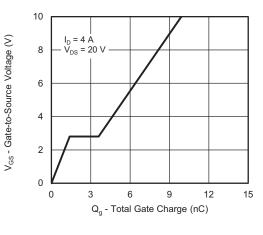
Capacitance



Transfer Characteristics



On-Resistance vs. Drain Current



Gate Charge

S16-1321-Rev. A, 04-Jul-16

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Document Number: 75159

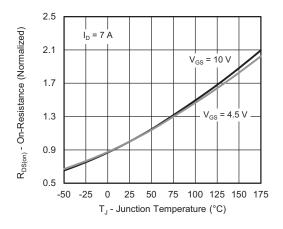
For technical questions, contact: <u>automostechsupport@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



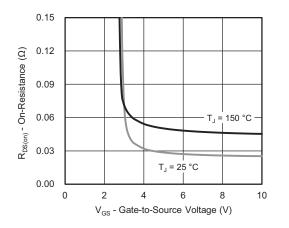
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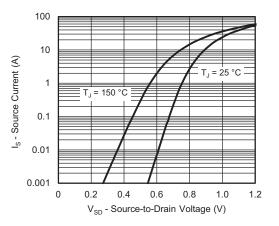
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



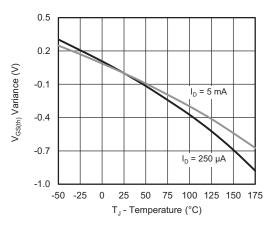
On-Resistance vs. Junction Temperature

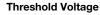


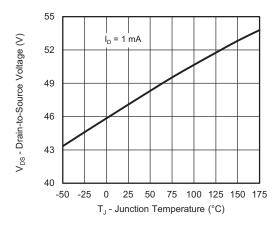
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage







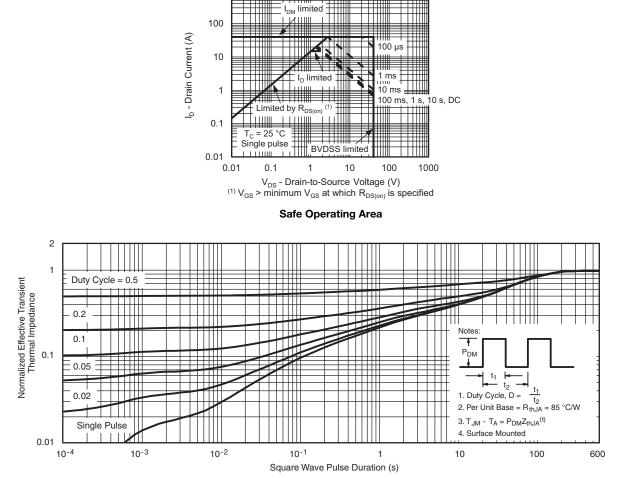
Drain Source Breakdown vs. Junction Temperature

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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)

1000



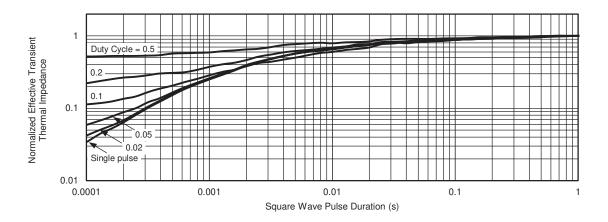
Normalized Thermal Transient Impedance, Junction-to-Ambient



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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

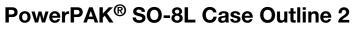
Note

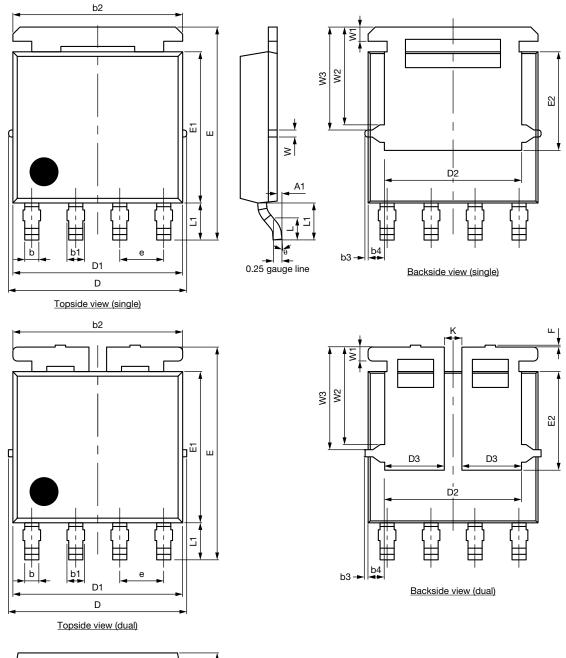
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

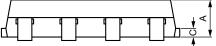
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?75159.









1 For technical questions, contact: <u>pmostechsupport@vishay.com</u>

Package Information



Vishay Siliconix

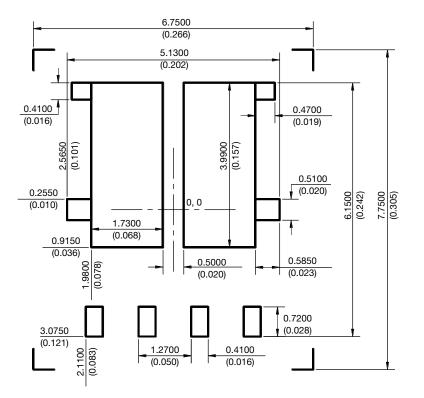
DIM.		MILLIMETERS			INCHES			
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.		
А	1.00	1.07	1.14	0.039	0.042	0.045		
A1	0.00	-	0.127	0.00	-	0.005		
b	0.33	0.41	0.48	0.013	0.016	0.019		
b1	0.44	0.51	0.58	0.017	0.020	0.023		
b2	4.80	4.90	5.00	0.189	0.193	0.197		
b3		0.094		0.004				
b4		0.47			0.019			
С	0.20	0.25	0.30	0.008	0.010	0.012		
D	5.00	5.13	5.25	0.197	0.202	0.207		
D1	4.80	4.90	5.00	0.189	0.193	0.197		
D2	3.86	3.96	4.06	0.152	0.156	0.160		
D3	1.63	1.73	1.83	0.064	0.068	0.072		
е		1.27 BSC			0.050 BSC			
E	6.05	6.15	6.25	0.238	0.242	0.246		
E1	4.27	4.37	4.47	0.168	0.172	0.176		
E2	2.75	2.85	2.95	0.108	0.112	0.116		
F	-	-	0.15	-	-	0.006		
L	0.62	0.72	0.82	0.024	0.028	0.032		
L1	0.92	1.07	1.22	0.036	0.042	0.048		
К	0.51			0.020				
W	0.23			0.009				
W1	0.41			0.016				
W2	2.82			0.111				
W3	2.96			0.117				
θ	0°	-	10°	0°	-	10°		

Note

• Millimeters will govern



RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L DUAL



Recommended Minimum Pads Dimensions in mm (inches) Keep-out 6.75 (0.266) x 7.75 (0.305)

Revision: 07-Feb-12



Vishay

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